

# SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

# N-Channel Silicon MOSFET 2SK4096LS — General-Purpose Switching Device **Applications**

# **Features**

- ON-resistance RDS(on)= $0.65\Omega$  (typ.)
- 10V drive

· Input capacitance Ciss=600pF

# **Specifications**

Absolute Maximum Ratings at Ta=25°C

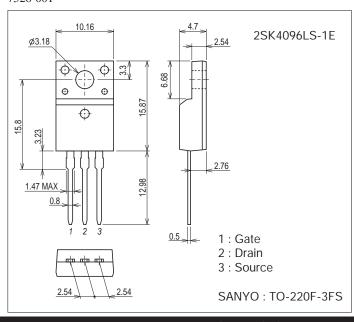
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		500	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±30	V
Drain Current (DC)	I <sub>Dc</sub> *1	Limited only by maximum temperature Tch=150°C	8	А
	I <sub>Dpack*2</sub>	Tc=25°C (SANYO's ideal heat dissipation condition)*3	7.1	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	32	А
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	33	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		354	mJ
Avalanche Current *5	IAV		8	Α

Note: \*1 Shows chip capability

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

# **Package Dimensions**

unit: mm (typ) 7528-001



# **Product & Package Information**

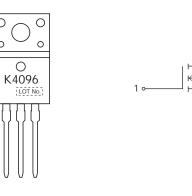
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

#### Marking

# **Electrical Connection**



# **SANYO Semiconductor Co., Ltd.**

http://www.sanyosemi.com/en/network/

<sup>\*2</sup> Package limited

<sup>\*3</sup> SANYO's condition is radiation from backside.

<sup>\*4</sup> VDD=50V, L=10mH, IAV=8A (Fig.1)

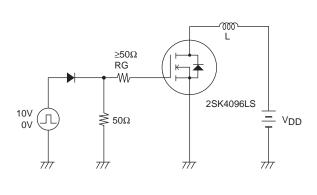
<sup>\*5</sup> L≤10mH, single pulse

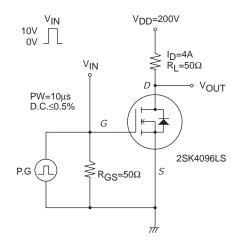
# Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	UTIIL	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	VGS=±30V, VDS=0V			±100	nA	
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3		5	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =4A	2.2	4.5		S	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)	I <sub>D</sub> =4A, V <sub>G</sub> S=10V		0.65	0.85	Ω	
Input Capacitance	Ciss			600		pF	
Output Capacitance	Coss	V <sub>DS</sub> =30V, f=1MHz		130		pF	
Reverse Transfer Capacitance	Crss			28		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			18.5		ns	
Rise Time	t <sub>r</sub>	Car Fig 2		46		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See Fig.2		75		ns	
Fall Time	t <sub>f</sub>			33		ns	
Total Gate Charge	Qg			24		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =8A		4.5		nC	
Gate-to-Drain "Miller" Charge	Qgd			14		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =8A, V <sub>GS</sub> =0V		0.9	1.2	V	

Fig.1 Unclamped Inductive Switching Test Circuit

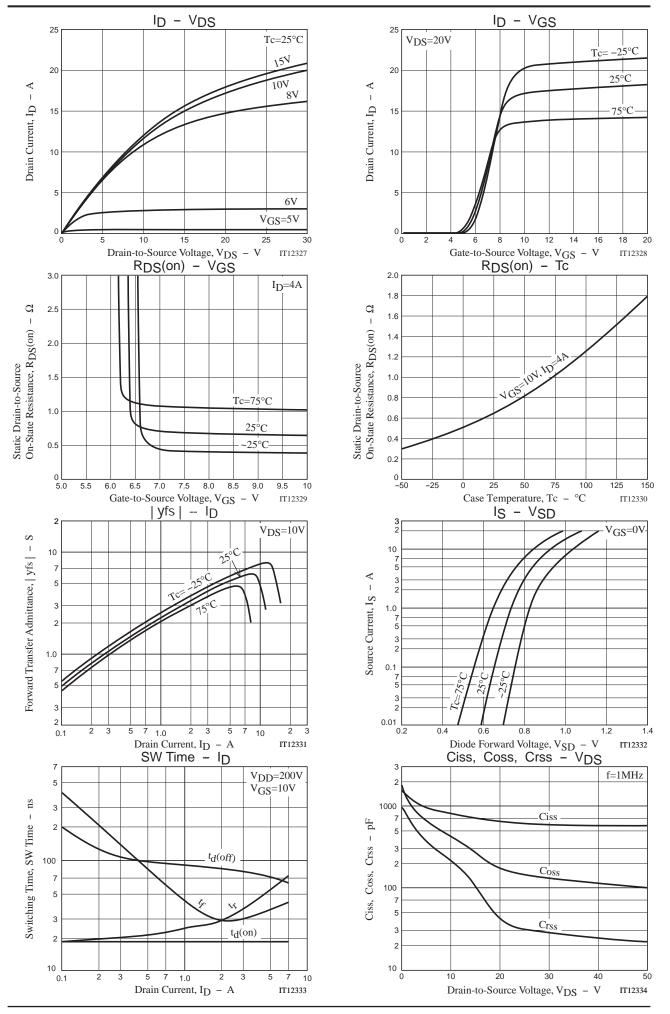
Fig.2 Switching Time Test Circuit

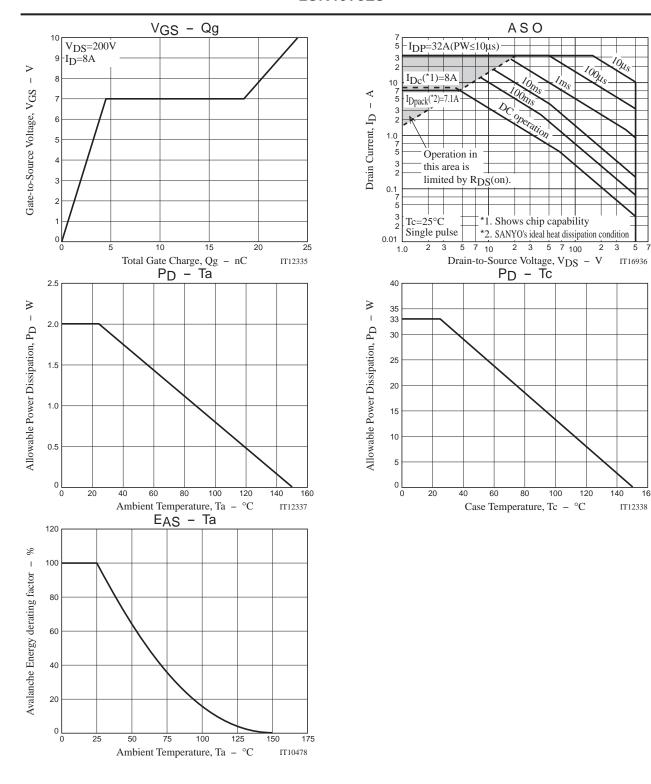




# **Ordering Information**

Device	Package	Shipping	memo
2SK4096LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free





140

160

IT12338

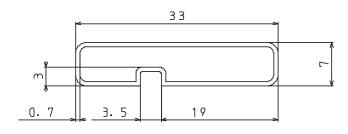
### Magazine Specification

2SK4096LS-1E

# 1. Packing Format

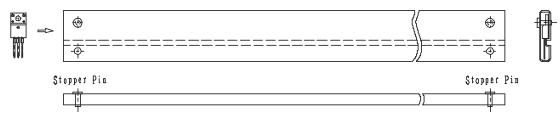
Package Name	Magazine Name	Maximum Number of devices contained (			Packing	format
144444 14444	1020 43 123 14223		Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3FS	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

# 



Tolerance=±0, 3mm
Thickness=0, 7±0, 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

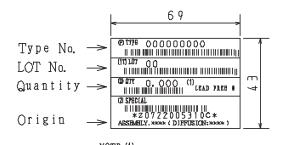
# 3. Storage method to magazine

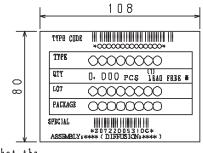


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



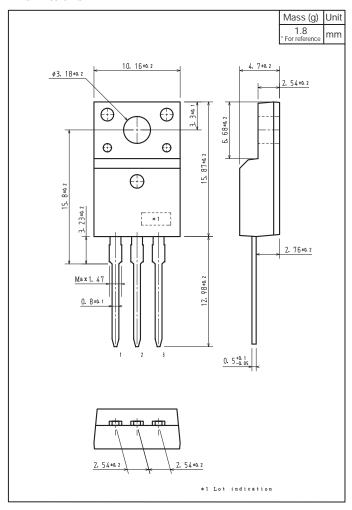


The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

# **Outline Drawing**

2SK4096LS-1E



Note on usage: Since the 2SK4096LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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